

Intrinsic Limit of Contact Resistance in Lateral Heterostructure of Metallic and Semiconducting PtSe₂

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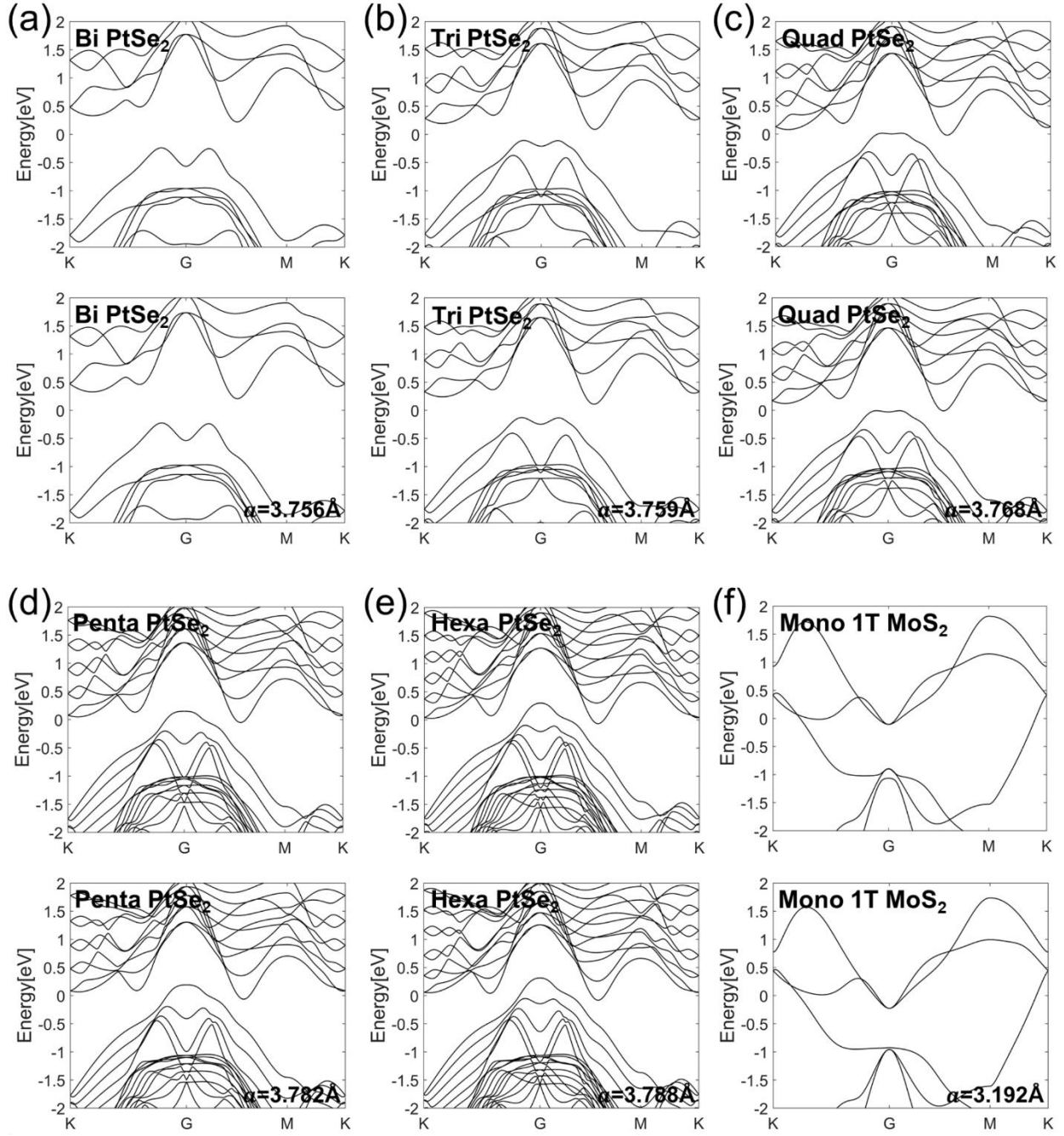


Figure S1. Band structures of (a) bilayer PtSe₂, (b) trilayer PtSe₂, (c) quadlayer PtSe₂, (d) pentalayer PtSe₂, (e) hexalayer PtSe₂ and (f) monolayer 1T MoS₂ without (top) and with (bottom) the optimization of the in-plane lattice constant.